



TO-92 Plastic-Encapsulate Transistors

BC368,-25 TRANSISTOR (NPN)

FEATURE

Power dissipation

P_{CM} : 0.625 W ($T_{amb}=25^{\circ}C$)

Collector current

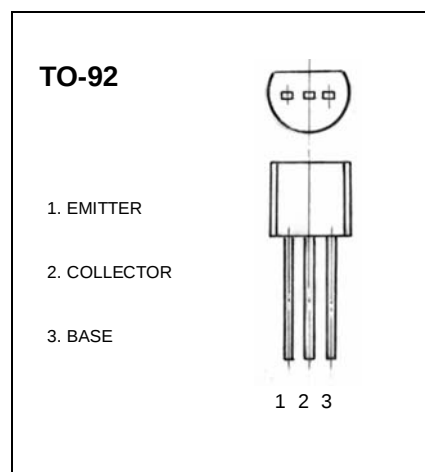
I_{CM} : 1 A

Collector-base voltage

$V_{(BR)CBO}$: 25 V

Operating and storage junction temperature range

T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C = 100\mu A, I_E = 0$	25		V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C = 10\text{ mA}, I_B = 0$	20		V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E = 100\mu A, I_C = 0$	5		V
Collector cut-off current	I_{CBO}	$V_{CB} = 25V, I_E = 0$		10	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = 5V, I_C = 0$		10	μA
DC current gain	$H_{FE(1)}$	$V_{CE}=10V, I_C = 5mA$	50		
	$H_{FE(2)}$ BC368 BC368-25	$V_{CE}=1V, I_C = 0.5mA$	85 170	375 375	
	$H_{FE(3)}$	$V_{CE}=1V, I_C = 1mA$	60		
Collector-emitter voltage	$V_{CE(sat)}$	$I_C = 1A, I_B = 100mA$		0.5	V
Base-emitter voltage	V_{BE}	$I_C = 1A, V_{CE} = 1V$		1	V
Transition frequency	f_T	$V_{CE} = 5V, I_C = 10mA$ $f = 20MHz$	65		MHz